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Applicant

Maeda et al.

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## U.S. PATENT APPLICATION DOCUMENTS

Examiner Initial*	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate

## U.S. PATENT DOCUMENTS

Examiner Initial*	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
Smm	US 6,565,822	5/20/2003	Hoshi et al.			

## FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
Smm	JP2001-039797	2/13/2001	JAPAN			Abstract	

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Smm	T Sato, "Effect of LAD on Epitaxial wafer", <i>Silicon Technology</i> , No. 16, 24 <sup>th</sup> April, 2000, 16 <sup>th</sup> Meeting of Silicon Technology Division, The Japan Society of Applied Physics [partial translation]
Smm	Asayama, et al., "Point Defect Behavior in Heavily Boron Doped Silicon Single Crystals", <i>Extended BSTRACTS (THE 60<sup>th</sup> Autumn Meeting, 1999)</i> , The Japan Society of Applied Physics, No. 0, "3p-ZY-4" [partial translation]
Smm	Dornberger, et al. "Influence of boron concentration on the oxidation-induced stacking fault ring in Czochralski silicon crystals", <i>Journal of Crystal Growth</i> , 180 (1997) pp 343-352

Examiner

s.m. malik

Date Considered

10/15/2007

\*Examiner:

Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.